Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Extended temperature range T_i = 175 °C
- Side wettable flanks for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 2 kV HBM (class H2)
- Trench MOSFET technology
- AEC-Q101 qualified

3. Applications

- Relay driver
- · High-speed line driver
- · Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-------------------|----------------------------------|---|-----|-----|-----|----------|
| V_{DS} | drain-source voltage | T _j = 25 °C | - | - | 30 | V |
| V_{GS} | gate-source voltage | | -20 | - | 20 | V |
| I _D | drain current | V _{GS} = 10 V; T _{sp} = 25 °C | - | - | 22 | Α |
| P _{tot} | total power dissipation | T _{sp} = 25 °C | - | - | 19 | W |
| Static chara | acteristics | | ' | ' | | <u> </u> |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 7.2 \text{ A}; T_j = 25 \text{ °C}$ | - | 16 | 22 | mΩ |



30 V, N-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|-----------------------|--|
| 1 | D | drain | 15736 | D I |
| 2 | D | drain | | |
| 3 | G | gate | 2 5 | G ← I ★ \ |
| 4 | S | source | 3 8 4 | \ \\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\ |
| 5 | D | drain | Transparent top view | |
| 6 | D | drain | DFN2020MD-6 (SOT1220) | S |
| 7 | D | drain | | 017aaa255 |
| 8 | S | source | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | |
|-------------|---------|---|---------|--|--|--|
| | Name | Description | Version | | | |
| BUK6D22-30E | | plastic, leadless thermal enhanced ultra thin small outline package; 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body | SOT1220 | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BUK6D22-30E | 6A |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|--|--|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | 30 | V |
| V _{GS} | gate-source voltage | | | -20 | 20 | V |
| I _D | drain current | V _{GS} = 10 V; T _{sp} = 25 °C | | - | 22 | Α |
| | | V _{GS} = 10 V; T _{sp} = 100 °C | | - | 15.7 | Α |
| | | V _{GS} = 10 V; T _{amb} = 25 °C | [1] | - | 7.2 | Α |
| I _{DM} | peak drain current | T_{sp} = 25 °C; single pulse; $t_p \le 10 \mu s$ | | - | 89 | Α |
| P _{tot} | total power dissipation | T _{sp} = 25 °C | | - | 19 | W |
| | | T _{amb} = 25 °C | [1] | - | 2 | W |
| Tj | junction temperature | | | -55 | 175 | °C |
| T _{amb} | ambient temperature | | | -55 | 175 | °C |
| T _{stg} | storage temperature | | | -65 | 175 | °C |
| Source-drair | n diode | | | | | _ |
| I _S | source current | T _{sp} = 25 °C | | - | 19 | Α |
| | | T _{amb} = 25 °C | [1] | - | 2 | Α |
| I _{SM} | peak source current | single pulse; $t_p \le 10 \mu s$; $T_{sp} = 25 \text{ °C}$ | | - | 75 | Α |
| ESD maximu | ım rating | | | | | _ |
| V_{ESD} | electrostatic discharge voltage | НВМ | [2] | - | 2000 | V |
| Avalanche ru | uggedness | | • | | | |
| E _{DS(AL)S} | non-repetitive drain- source avalanche energy | $T_{j(init)}$ = 25 °C; I_D = 1.17 A; DUT in valanche (unclamped) | | - | 17.4 | mJ |

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².
- [2] Measured between all pins.

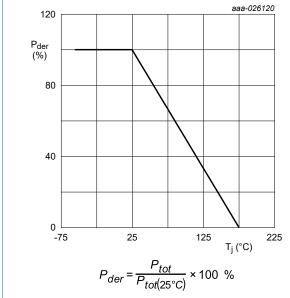


Fig. 1. Normalized total power dissipation as a function of junction temperature

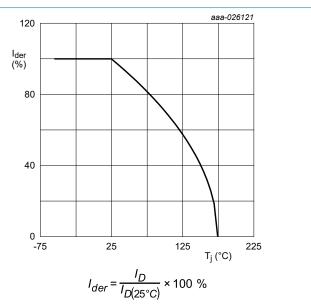


Fig. 2. Normalized continuous drain current as a function of junction temperature

30 V, N-channel Trench MOSFET

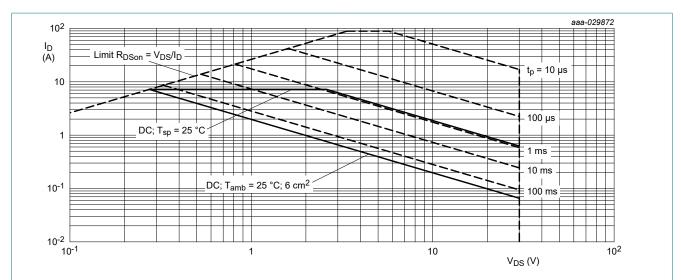


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

30 V, N-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|----------------|--|-------------|-----|-----|-----|-----|------|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | [1] | - | 66 | 76 | K/W |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | | | - | 4 | 8 | K/W |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

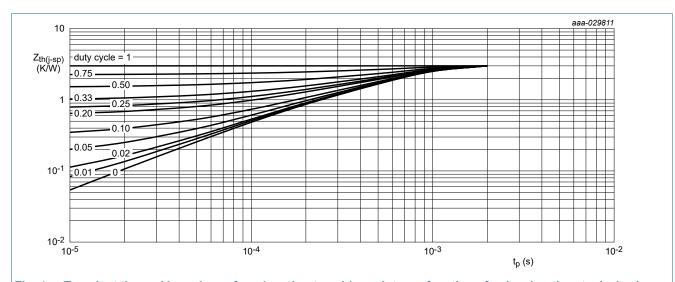


Fig. 4. Transient thermal impedance from junction to solder point as a function of pulse duration; typical values

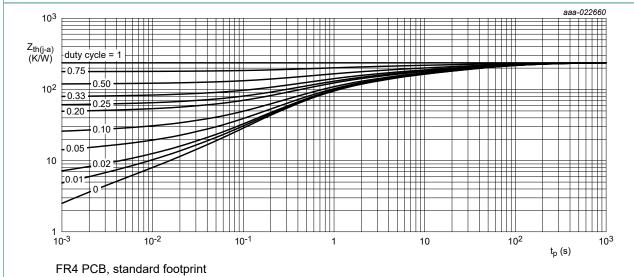


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

30 V, N-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|-----------------------------------|---|-----|-----|-----|------|
| Static chara | acteristics | | | | | |
| V _{(BR)DSS} | drain-source breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$ | 30 | - | - | V |
| V_{GSth} | gate-source threshold voltage | $I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$ | 1 | 1.5 | 2.5 | V |
| I _{DSS} | drain leakage current | V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C | - | - | 1 | μΑ |
| | | V _{DS} = 30 V; V _{GS} = 0 V; T _j = 125 °C | - | - | 20 | μΑ |
| I _{GSS} | gate leakage current | V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 10 | μΑ |
| | | V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -10 | μΑ |
| | | V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 2 | μΑ |
| | | V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -2 | μΑ |
| Doon | drain-source on-state resistance | V _{GS} = 10 V; I _D = 7.2 A; T _j = 25 °C | - | 16 | 22 | mΩ |
| | | V _{GS} = 10 V; I _D = 7.2 A; T _j = 175 °C | - | 28 | 38 | mΩ |
| | | $V_{GS} = 4.5 \text{ V}; I_D = 6.2 \text{ A}; T_j = 25 \text{ °C}$ | - | 22 | 30 | mΩ |
| 9 _{fs} | forward transconductance | $V_{DS} = 10 \text{ V}; I_D = 7.2 \text{ A}; T_j = 25 ^{\circ}\text{C}$ | - | 24 | - | S |
| R _G | gate resistance | f = 1 MHz | - | 2 | - | Ω |
| Dynamic ch | naracteristics | | | | | |
| Q _{G(tot)} | total gate charge | V _{DS} = 15 V; I _D = 7.2 A; V _{GS} = 10 V; | - | 9.5 | 14 | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C | - | 1 | - | nC |
| Q_{GD} | gate-drain charge | | - | 2.2 | - | nC |
| C _{iss} | input capacitance | V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V; | - | 440 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 110 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 75 | - | pF |
| t _{d(on)} | turn-on delay time | V _{DS} = 15 V; I _D = 7.2 A; V _{GS} = 10 V; | - | 4 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$ | - | 18 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 15 | - | ns |
| t _f | fall time | | - | 7 | - | ns |
| Source-dra | in diode | | 1 | | | |
| V _{SD} | source-drain voltage | $I_S = 2 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | 8.0 | 1.2 | V |
| t _{rr} | reverse recovery time | $I_S = 2 \text{ A}; \text{ d}I_S/\text{d}t = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$ | - | 11 | - | ns |
| Q _r | recovered charge | V _{DS} = 15 V; T _j = 25 °C | - | 4 | - | nC |

30 V, N-channel Trench MOSFET

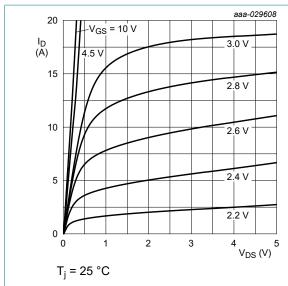


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

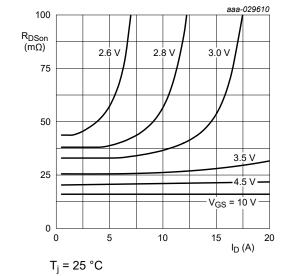


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

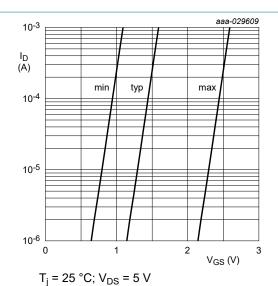


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

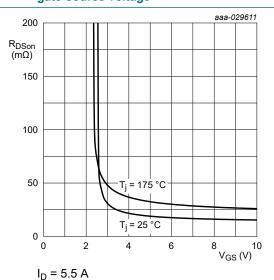


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

30 V, N-channel Trench MOSFET

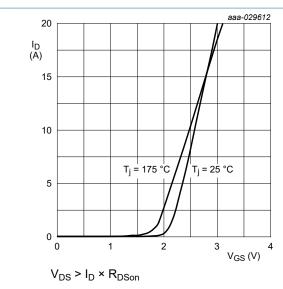


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

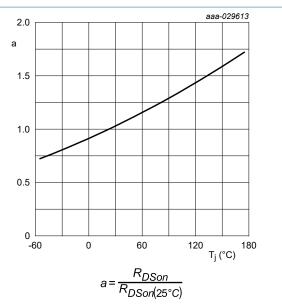


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

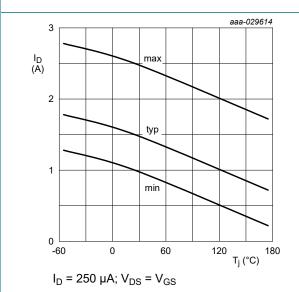


Fig. 12. Gate-source threshold voltage as a function of junction temperature

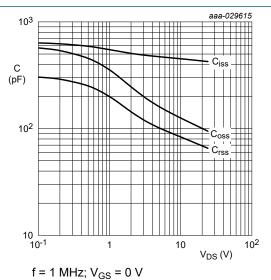


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

30 V, N-channel Trench MOSFET

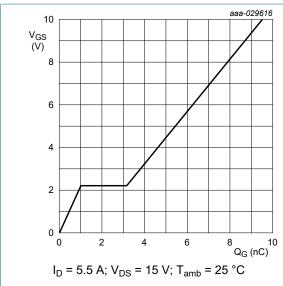


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

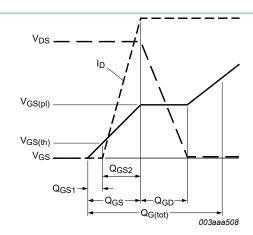


Fig. 15. Gate charge waveform definitions

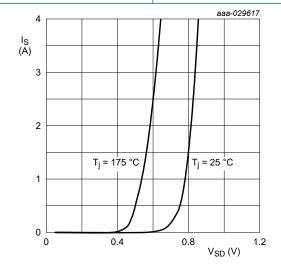
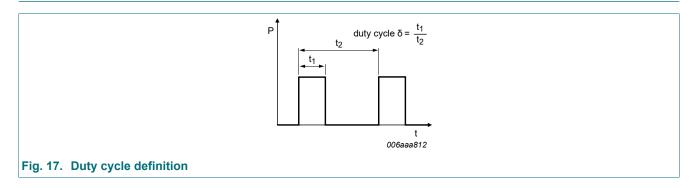


Fig. 16. Source current as a function of source-drain voltage; typical values

30 V, N-channel Trench MOSFET

11. Test information

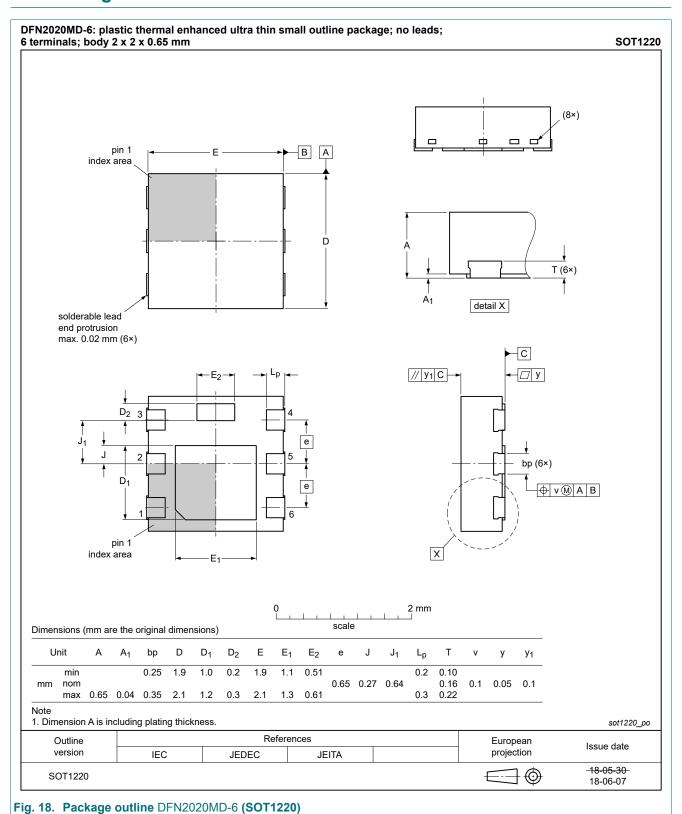


Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

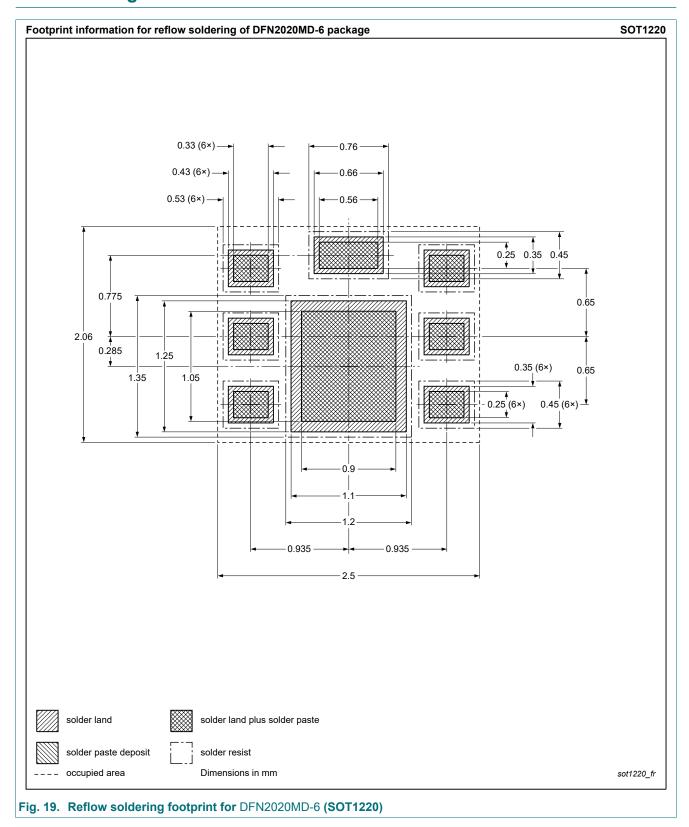
30 V, N-channel Trench MOSFET

12. Package outline



30 V, N-channel Trench MOSFET

13. Soldering



30 V, N-channel Trench MOSFET

14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|-----------------|--------------|--------------------|---------------|------------|
| BUK6D22-30E v.1 | 20190410 | Product data sheet | - | - |

30 V, N-channel Trench MOSFET

15. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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30 V, N-channel Trench MOSFET

Contents

| 1. | General description | 1 |
|-----|-------------------------|------|
| 2. | Features and benefits | 1 |
| 3. | Applications | 1 |
| 4. | Quick reference data | 1 |
| 5. | Pinning information | 2 |
| 6. | Ordering information | 2 |
| 7. | Marking | 2 |
| 8. | Limiting values | 3 |
| 9. | Thermal characteristics | 5 |
| 10. | Characteristics | е |
| 11. | Test information | . 10 |
| 12. | Package outline | . 11 |
| 13. | Soldering | . 12 |
| 14. | Revision history | .13 |
| 15. | Legal information | .14 |
| | | |

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